ABSTRACT

SELECTIVE WSIX DEPOSITION

A method for selectively depositing WSi_x is described. Semiconductor device structures are provided in and on a semiconductor substrate wherein WSi_x is to be deposited overlying a first portion of the substrate and wherein WSi_x is not to be deposited overlying a second portion of the substrate. A layer of organic material is provided over the surface of the substrate overlying the second portion of the substrate. A layer of WSi_x is deposited over the surface of the substrate wherein the WSi_x is deposited overlying the first portion of the substrate and wherein the presence of the organic material layer prevents the WSi_x from depositing overlying the second portion of the substrate completing the selective WSi_x deposition in the fabrication of an integrated circuit device.

(FIGURE 1 IS SUGGESTED FOR PUBLICATION)